

QUAD 2-INPUT NOR GATE

- HIGH SPEED: t_{PD} = 3.6ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: $I_{CC} = 2 \mu A \text{ (MAX.)}$ at $T_A = 25 \text{°C}$
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28% V_{CC} (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 8mA (MIN)
- BALANCED PROPAGATION DELAYS: tpi H ≅ tpHi
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 2V to 5.5V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 02
- IMPROVED LATCH-UP IMMUNITY
- LOW NOISE: V_{OLP} = 0.8V (MAX.)

DESCRIPTION

The 74VHC02 is an advanced high-speed CMOS QUAD 2-INPUT NOR GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provides high noise immunity and stable output.

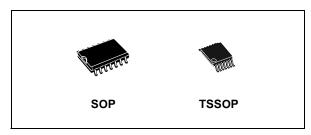


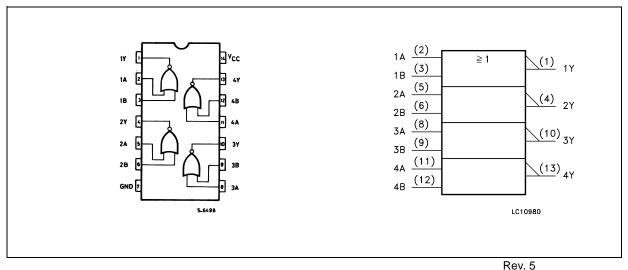
Table 1: Order Codes

PACKAGE	T & R
SOP	74VHC02MTR
TSSOP	74VHC02TTR

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

Figure 1: Pin Connection And IEC Logic Symbols



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Figure 2: Input Equivalent Circuit

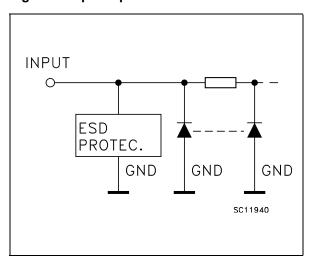


Table 2: Pin Description

PIN N°	SYMBOL	NAME AND FUNCTION
2, 5, 8, 11	1A to 4A	Data Inputs
3, 6, 9, 12	1B to 4B	Data Inputs
1, 4, 10, 13	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

Table 3: Truth Table

Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

Table 5: Recommended Operating Conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V_{CC} = 3.3 \pm 0.3V) (V_{CC} = 5.0 \pm 0.5V)	0 to 100 0 to 20	ns/V

¹⁾ $\rm V_{IN}$ from 30% to 70% of $\rm V_{CC}$

Table 6: DC Specifications

		Т	est Condition				Value				
Symbol	Parameter	v _{cc}		T _A = 25°C			-40 to	85°C	-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	3.0 to 5.5		0.7V _{CC}			0.7V _{CC}		0.7V _{CC}		V
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	3.0 to 5.5				0.3V _{CC}		0.3V _{CC}		0.3V _{CC}	V
V _{OH}	High Level Output	2.0	I _O =-50 μA	1.9	2.0		1.9		1.9		
	Voltage	3.0	I _O =-50 μA	2.9	3.0		2.9		2.9		
		4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		V
		3.0	I _O =-4 mA	2.58			2.48		2.4		
		4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	
	Voltage	3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μΑ
Icc	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			2		20		20	μΑ

Table 7: AC Electrical Characteristics (Input $t_r = t_f = 3ns$)

		Test Condition			Value							
Symbol	Parameter	ν _{cc}	CL		Т	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		V _{CC}	(pF)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay	3.3 ^(*)	15			5.6	7.9	1.0	9.5	1.0	9.5	
	Time	3.3 ^(*)	50			8.1	11.4	1.0	13.0	1.0	13.0	nc
		5.0 ^(**)	15			3.6	5.5	1.0	6.5	1.0	6.5	ns
		5.0 ^(**)	50			4.5	7.5	1.0	8.5	1.0	8.5	

^(*) Voltage range is $3.3\text{V} \pm 0.3\text{V}$ (**) Voltage range is $5.0\text{V} \pm 0.5\text{V}$

Table 8: Capacitive Characteristics

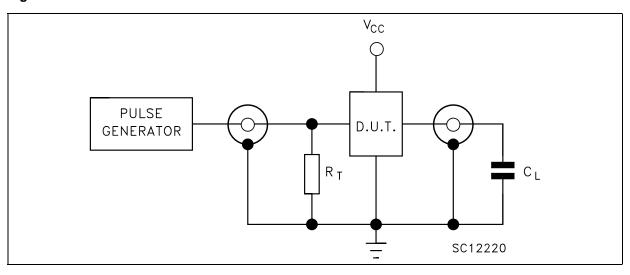
		Test Condition		Value						
Symbol	Parameter		Т	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			6	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			19						pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per gate)

Table 9: Dynamic Switching Characteristics

			Test Condition		Value						
Symbol Parameter	v _{cc}		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{OLP}	Dynamic Low	- 0			0.3	8.0					.,
V _{OLV}	Voltage Quiet Output (note 1, 2)	5.0		-0.8	-0.3						V
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	5.0	C _L = 50 pF	3.5							V
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	5.0				1.5					V

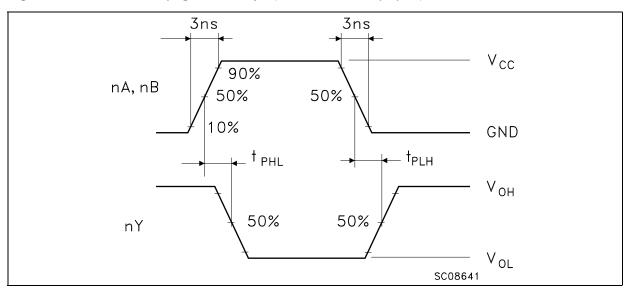
Figure 3: Test Circuit



 C_L =15/ 50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically $50\Omega)$

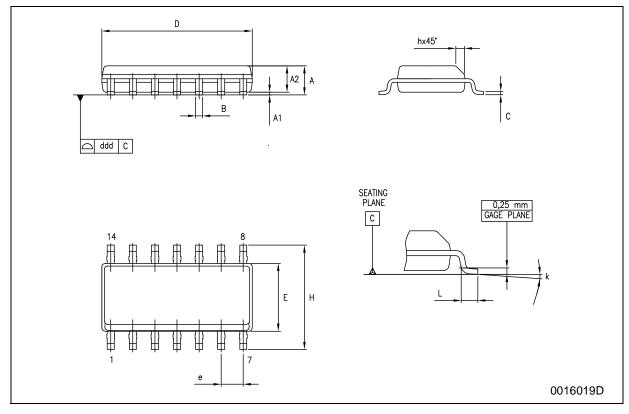
¹⁾ Worst case package.
2) Max number of outputs defined as (n). Data inputs are driven 0V to 5.0V, (n-1) outputs switching and one output at GND.
3) Max number of data inputs (n) switching. (n-1) switching 0V to 5.0V. Inputs under test switching: 5.0V to threshold (V_{ILD}), 0V to threshold (V_{IHD}) , f=1MHz.





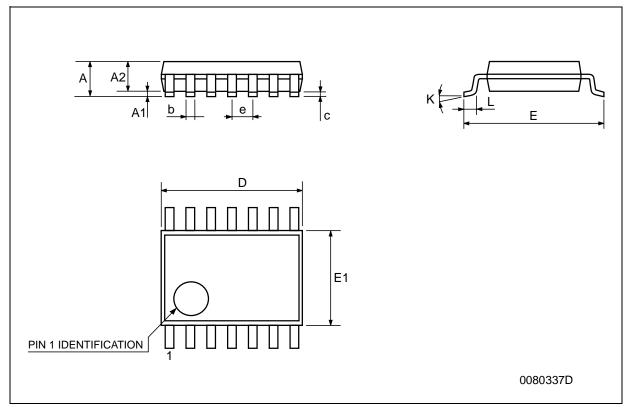
SO-14 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	1.35		1.75	0.053		0.069
A1	0.1		0.25	0.004		0.010
A2	1.10		1.65	0.043		0.065
В	0.33		0.51	0.013		0.020
С	0.19		0.25	0.007		0.010
D	8.55		8.75	0.337		0.344
E	3.8		4.0	0.150		0.157
е		1.27			0.050	
Н	5.8		6.2	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.4		1.27	0.016		0.050
k	0°		8°	0°		8°
ddd			0.100			0.004



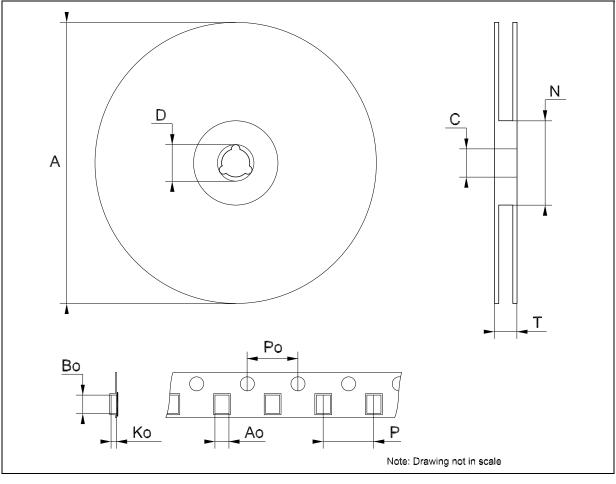
TSSOP14 MECHANICAL DATA

DIM.		mm.			inch	
DIIVI.	MIN.	TYP	TYP MAX.		MIN. TYP.	
А			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
С	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
е		0.65 BSC			0.0256 BSC	
К	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



Tape & Reel SO-14 MECHANICAL DATA

	mm.		inch				
MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
		330			12.992		
12.8		13.2	0.504		0.519		
20.2			0.795				
60			2.362				
		22.4			0.882		
6.4		6.6	0.252		0.260		
9		9.2	0.354		0.362		
2.1		2.3	0.082		0.090		
3.9		4.1	0.153		0.161		
7.9		8.1	0.311		0.319		
	12.8 20.2 60 6.4 9 2.1 3.9	MIN. TYP 12.8 20.2 60 6.4 9 2.1 3.9	MIN. TYP MAX. 330 12.8 13.2 20.2 60 22.4 6.4 6.6 9 9 9.2 2.1 2.3 3.9 4.1	MIN. TYP MAX. MIN. 330 12.8 13.2 0.504 20.2 0.795 0.795 60 2.362 22.4 6.6 0.252 9 9.2 0.354 2.1 2.3 0.082 3.9 4.1 0.153	MIN. TYP MAX. MIN. TYP. 12.8 13.2 0.504 0.795		



Tape & Reel TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Во	5.3		5.5	0.209		0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319

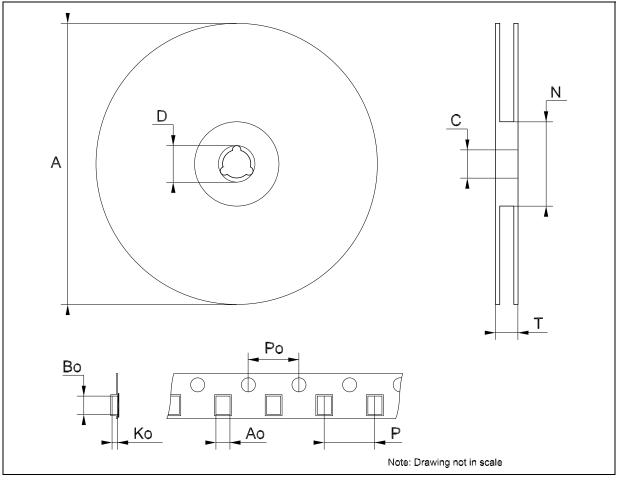


Table 10: Revision History

Date	Revision	Description of Changes
12-Nov-2004	5	Order Codes Revision - pag. 1.

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